

BASE CURRENT REVERSAL SRAM  
MEMORY CELL AND METHOD

ABSTRACT OF THE DISCLOSURE

A SRAM memory cell including an access device formed on a storage device is described. The storage device has at least two stable states that may be used to store information. In operation, the access device is switched ON to allow a signal representing data to be coupled to the storage device. The storage device switches to a state representative of the signal and maintains this state after the access device is switched OFF. When the access device is switched ON, the state of the storage device may be sensed to read the data stored in the storage device. The memory cell may be formed to be unusually compact and has a reduced power supply requirements compared to conventional SRAM memory cells. As a result, a compact and robust SRAM having reduced standby power requirements is realized.